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2364 STATIC READ ONLY MEMORY (8192x8)

DESCRIPTION

The 2364 high performance read only memory is organized 8192 words by 8 bits with access times of less than 350 ns. This ROM is designed to be compatible with all microprocessor and similar applications where high performance, large bit storage and simple interfacing are important design considerations. This device offers TTL input and output levels.

The 2364 operates totally asynchronously. No clock input is required. The programmable chip select input allows two 64K ROMs to be OR-tied without external decoding.

Designed to replace two 2732 32K EPROMS, the 2364 can eliminate the need to redesign printed circuit boards for volume mask programmed ROMs after prototyping with EPROMS.

- 8192 x 8 Bit Organization
- Single +5 Volt Supply
- Access Time — 450 ns, 350 ns
- Completely TTL Compatible
- Totally Static Operation
- Three-State Outputs for Wire-OR Expansion
- One Programmable Chip Select
- Pin Compatible with 2716 & 2732 EPROM
- Replacement for Two 2732s
- 2716/2732 EPROMS Accepted as Program Data Inputs
- 400mV Noise Immunity on Inputs

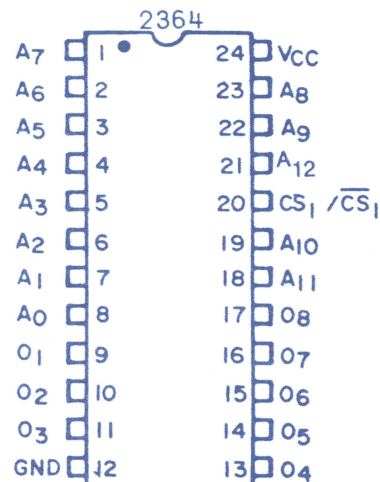
ORDERING INFORMATION

MXS 2364

FREQUENCY RANGE
NO SUFFIX = 450ns
A = 350ns

PACKAGE DESIGNATOR
C = CERAMIC
P = PLASTIC

PIN CONFIGURATION



ABSOLUTE MAXIMUM RATINGS

Ambient Temperature under Bias	°C to +70°C
Storage Temperature	−65°C to +150°C
Supply Voltage to Ground Potential	−0.5V to +7.0V
Applied Output Voltage	−0.5V to +7.0V
Applied Input Voltage	−0.5V to +7.0V
Power Dissipation	1.0W

COMMENT

Stresses above those listed under “Absolute Maximum Ratings” may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

D. C. CHARACTERISTICS (T_A = 0°C to +70°C, V_{CC} = 5.0V ± 5%, unless otherwise specified)

Symbol	Parameter	Min.	Max.	Units	Test Conditions
I _{CC1}	Power Supply Current		100	mA	V _{IN} = V _{CC} , V _O = Open, T _A = 0°C
I _{CC2}	Power Supply Current		95	mA	V _{IN} = V _{CC} , V _O = Open, T _A = 25°C
I _O	Output Leakage Current		10	μA	Chip Deselected, V _O = 0 to V _{CC}
I _I	Input Load Current		10	μA	V _{CC} = Max. V _{IN} = 0 to V _{CC}
V _{OL}	Output Low Voltage		0.4	Volts	V _{CC} = Min. I _{OL} = 2.1mA
V _{OH}	Output High Voltage	2.4		Volts	V _{CC} = Min. I _{OH} = −400μA
V _{IL}	Input Low Voltage	−0.5	0.8	Volts	See Note 1
V _{IH}	Input High Voltage	2.0	V _{CC} +1	Volts	

A. C. CHARACTERISTICS (T_A = 0°C to +70°C, V_{CC} = 5.0V ± 5%, unless otherwise specified)

Symbol	Parameter	2364		2364A		Units	Test Conditions
		Min.	Max.	Min.	Max.		
t _{ACC}	Address Access Time		450		350	ns	See Note 2
t _{CO}	Chip Select Delay		200		200	ns	
t _{DF}	Chip Deselect Delay		175		175	ns	
t _{OH}	Previous Data Valid After Address Change Delay	40		40		ns	

CAPACITANCE (T_A = 25°C, f = 1.0MHz, See Note 3)

Symbol	Parameter	Min.	Max.	Units	Test Conditions
C _{IN}	Input Capacitance		8	pF	All Pins except Pin under
C _{OUT}	Output Capacitance		10	pF	Test Tied to AC Ground

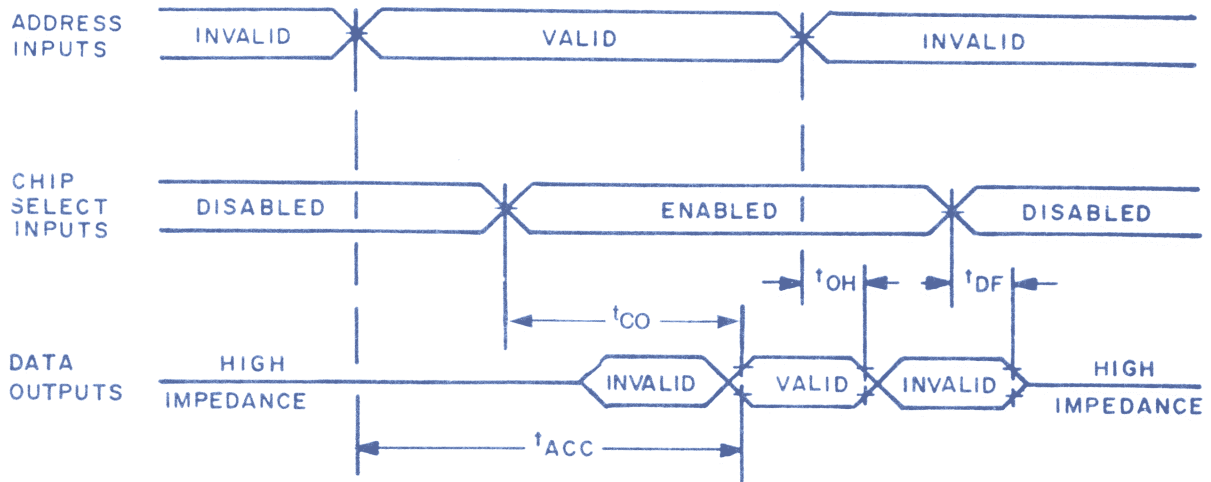
Note 1: Input levels that swing more negative than −0.5V will be clamped and may cause damage to the device.

Note 2: Loading 1 TTL + 100 pF, input transition time: 20 ns

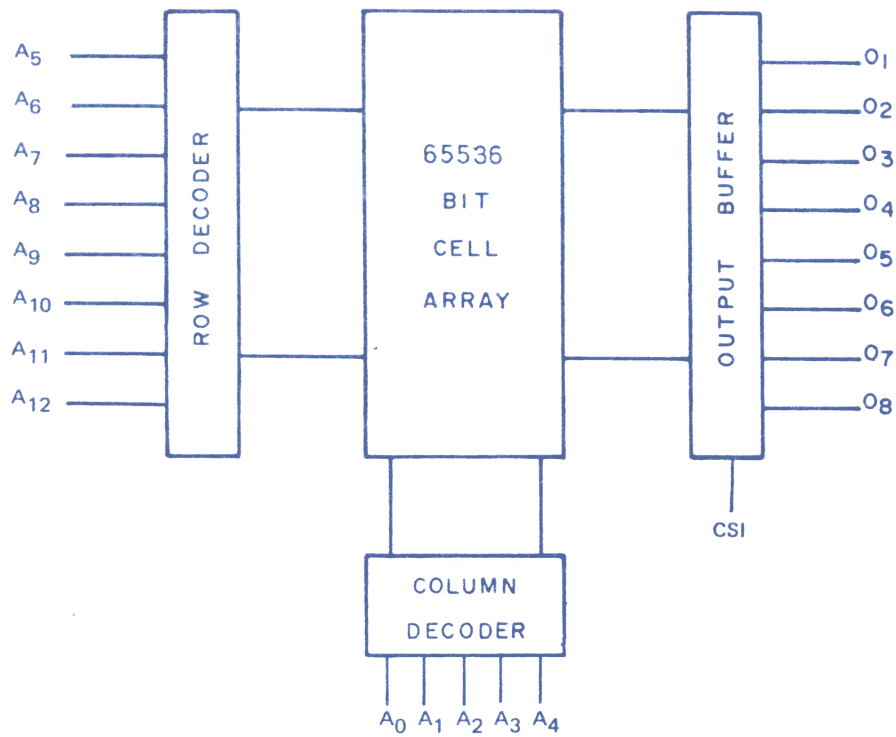
Timing measurement levels: input 1.5V, output 0.8V and 2.0V. C_L = 100 pF

Note 3: This parameter is periodically sampled and is not 100% tested.

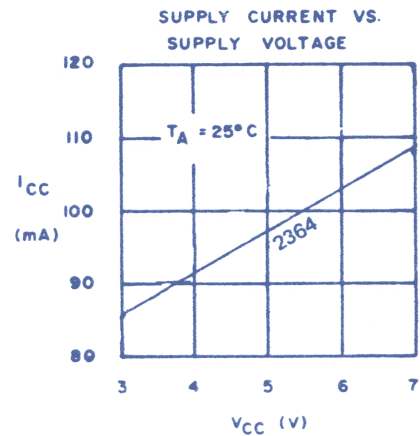
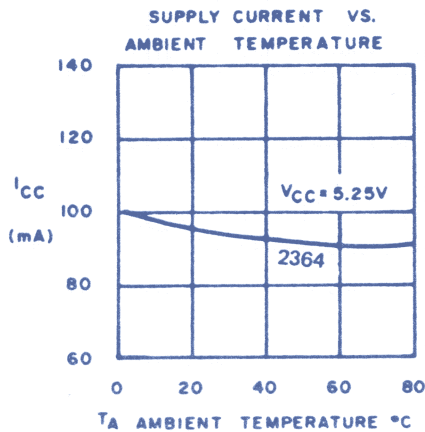
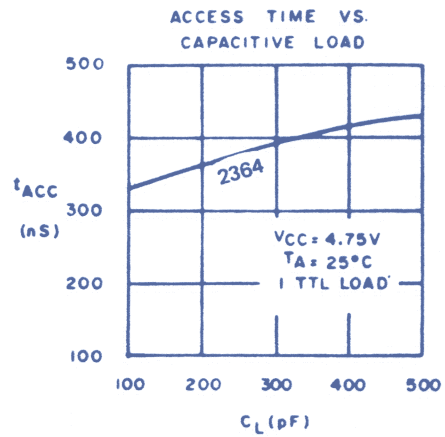
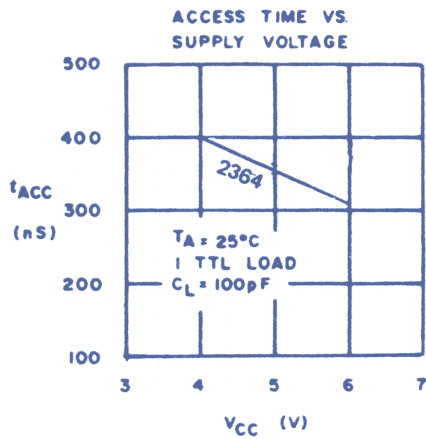
TIMING DIAGRAM



BLOCK DIAGRAM



TYPICAL CHARACTERISTICS



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